Product data sheet

1. General description

Hyperfast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Low leakage current
- Low thermal resistance
- · Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|-------------------------------------|---|-----|------|------|------|
| V_R | reverse voltage | DC | - | - | 600 | V |
| I _{F(AV)} | average forward current | δ = 0.5; T _{mb} ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | - | - | 30 | Α |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4 | - | - | 270 | А |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | - | - | 300 | Α |
| Static characte | eristics | | | | | |
| V _F | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u> | - | 2 | 2.75 | V |
| | | I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u> | - | 1.38 | 1.8 | V |
| Dynamic chara | acteristics | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $\frac{\text{Fig. 7}}{}$ | - | 18 | 22 | ns |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|----------------|
| 1 | K | cathode | | K — A |
| 2 | Α | anode | | 001aaa020 |
| mb | mb | mounting base; connected to cathode | TO-247 (SOD142) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | | |
|-------------|---------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| BYC30W-600P | TO-247 | Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247 | SOD142 | | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BYC30W-600P | BYC30W-600P |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|-------------------------------------|---|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V_{RWM} | crest working reverse voltage | | - | 600 | V |
| V_R | reverse voltage | DC | - | 600 | V |
| I _{F(AV)} | average forward current | $δ = 0.5$; $T_{mb} \le 115$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | - | 30 | Α |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le 115$ °C; square-wave pulse | - | 60 | Α |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4 | - | 270 | Α |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | - | 300 | Α |
| T _{stg} | storage temperature | | -65 | 175 | °C |
| T _j | junction temperature | | - | 175 | °C |

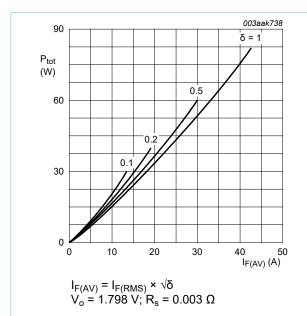


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

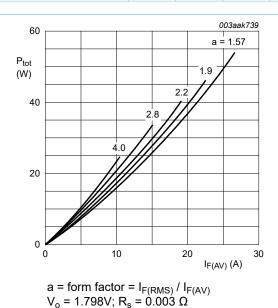


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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Hyperfast power diode

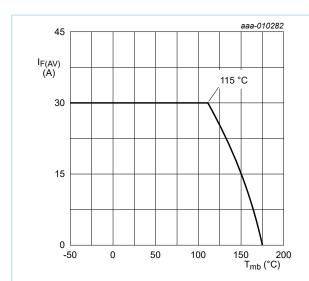


Fig. 3. Forward current as a function of mounting base temperature; maximum values

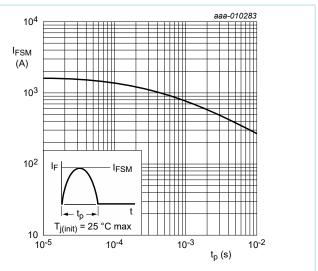
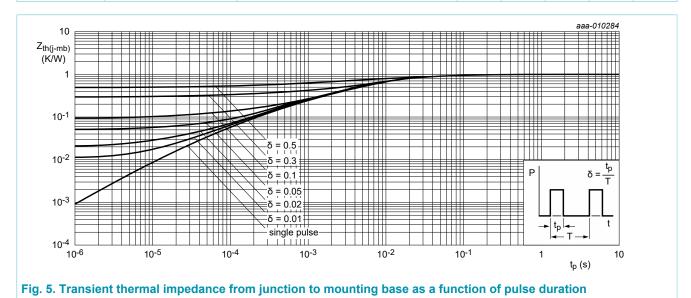


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|--------------------------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | with heatsink compound; Fig. 5 | - | - | 1 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | - | 45 | - | K/W |



BYC30W-600P

10. Characteristics

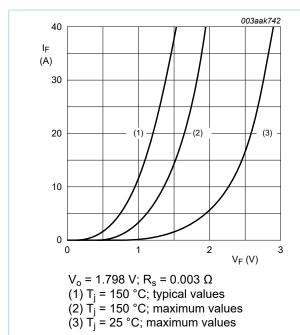
Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------|--|--|------|------|------|
| Static chara | acteristics | 1 | | | | |
| V _F | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u> | - | 2 | 2.75 | V |
| | | I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u> | - | 1.38 | 1.8 | V |
| I _R | reverse current | V _R = 600 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _R = 600 V; T _j = 150 °C | - | - | 1 | mA |
| Dynamic ch | aracteristics | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 18 | 22 | ns |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 35 | - | ns |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$ | - | 70 | - | ns |
| | | $I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 29 | - | ns |
| I _{RM} | peak reverse recovery current | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 3.5 | - | А |
| | | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$ | - | 7.6 | - |
| Q _r | recovered charge | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 50 | - | nC |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$ | - | 280 | - | nC |

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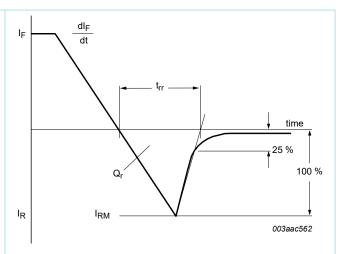
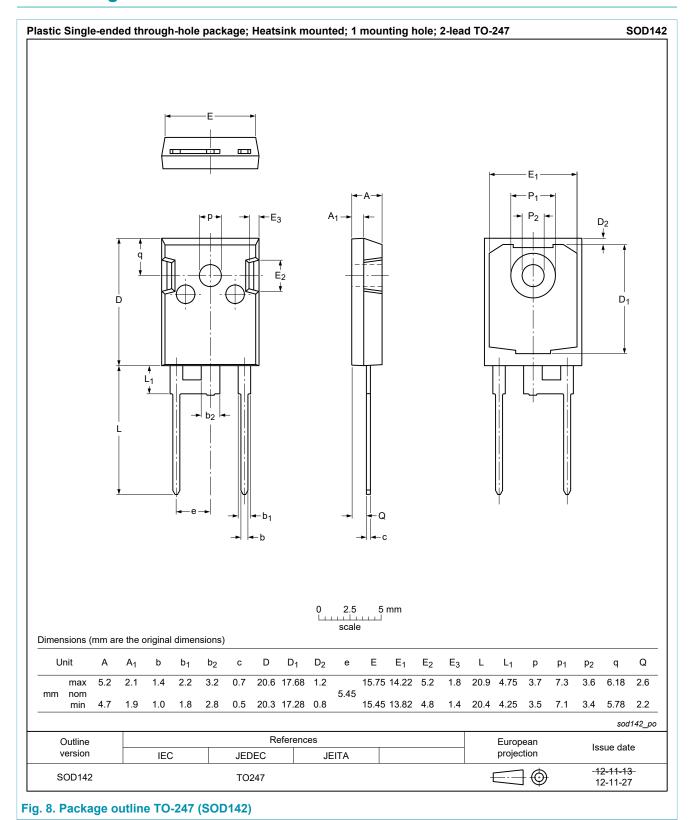


Fig. 7. Reverse recovery definitions; ramp recovery

Fig. 6. Forward current as a function of forward voltage

11. Package outline



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12. Legal information

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|--------------------------------------|--------------------|---|
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